

# **CAT25320**

# 32K-Bit SPI Serial CMOS EEPROM

# RoHS Compliance

# **FEATURES**

- 10 MHz SPI compatible
- 1.8 to 5.5 volt operation
- Hardware and software protection
- Low power CMOS technology
- SPI modes (0,0 &1,1)
- Industrial temperature range
- 1,000,000 program/erase cycles
- 100 year data tetention
- Self-timed write cycle
- RoHS compliant "Green" & "Gold" 8-pin PDIP and 8-pin SOIC packages
- 64-Byte page write buffer
- Block write protection
  - Protect 1/4, 1/2 or all of EEPROM array

# **DESCRIPTION**

The CAT25320 is a 32K-Bit SPI Serial CMOS EEPROM internally organized as 4Kx8 bits. Catalyst's advanced CMOS Technology substantially reduces device power requirements. The CAT25320 features a 64-byte page write buffer. The device operates via the SPI bus serial interface and is enabled though a Chip Select (CS). In addition to the Chip Select, the clock input (SCK), data in (SI) and data out (SO) are required to access the device. The HOLD pin may be used to suspend any serial communication without resetting the serial sequence. The CAT25320 is designed with software and hardware write protection features including Block write protection. The device is available in 8-pin DIP, SOIC and TSSOP packages.

#### PIN CONFIGURATION

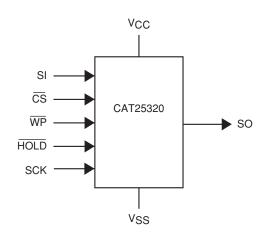
SOIC (V) TSSOP (Y)					
CS	1	8	$V_{CC}$		
SO	2	7	HOLD		
$\overline{WP}$	3	6	SCK		
$V_{SS}$	4	5	SI		

DDID (L)

#### **PIN FUNCTIONS**

Pin Name	Function			
SO	Serial Data Output			
SCK	Serial Clock			
WP	Write Protect			
Vcc	+1.8V to +6.0V Power Supply			
V <sub>SS</sub>	Ground			
CS	Chip Select			
SI	Serial Data Input			
HOLD	Suspends Serial Input			

# **FUNCTIONAL SYMBOL**





#### **ABSOLUTE MAXIMUM RATINGS\***

Storage Temperature	-65°C to +150°C
Voltage on Any Pin with Respect to Ground <sup>(1)</sup>	-0.5 V to +6.5 V

<sup>\*</sup> Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside of those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.

#### RELIABILITY CHARACTERISTICS(2)

Symbol	I Parameter Min		Units	
N <sub>END</sub> (*)	Endurance	1,000,000	Program/ Erase Cycles	
T <sub>DR</sub>	Data Retention	100	Years	

<sup>(\*)</sup> Page Mode,  $V_{CC} = 5 \text{ V}, 25^{\circ}\text{C}$ 

#### D.C. OPERATING CHARACTERISTICS

 $V_{CC} = 1.8 \text{ V}$  to 5.5 V,  $T_A = -40^{\circ}\text{C}$  to 85°C, unless otherwise specified.

Symbol	Parameter	Test Conditions	Min	Max	Units
I <sub>CC</sub>	Supply Current	Read, Write, $V_{CC} = 5.0V$ , $f_{SCK} = 10MHz$ , SO open		2	mA
I <sub>SB1</sub>	Standby Current	$V_{IN} = GND \text{ or } V_{CC}$ , $\overline{CS} = V_{CC}$ , $\overline{WP} = V_{CC}$ , $V_{CC} = 5V$		2	μА
I <sub>SB2</sub>	Standby Current	$V_{IN} = GND \text{ or } V_{CC}$ , $\overline{CS} = V_{CC}$ , $\overline{WP} = GND$ , $V_{CC} = 5V$		4	μА
IL	Input Leakage Current	$V_{IN} = GND \text{ or } V_{CC}$	-2	2	μΑ
I <sub>LO</sub>	Output Leakage Current	$\overline{\text{CS}} = V_{\text{CC}}$ , $V_{\text{OUT}} = \text{GND}$ or $V_{\text{CC}}$	-1	1	μΑ
V <sub>IL</sub> (3)	Input Low Voltage		-0.5	0.3V <sub>CC</sub>	V
V <sub>IH</sub> (3)	Input High Voltage		0.7V <sub>CC</sub>	V <sub>CC</sub> + 0.5	V
V <sub>OL1</sub>	Output Low Voltage	$V_{CC} > 2.5V, I_{OL} = 3.0mA$		0.4	V
V <sub>OH1</sub>	Output High Voltage	V <sub>CC</sub> > 2.5V, I <sub>OH</sub> = -1.6mA	V <sub>CC</sub> - 0.8V		V
V <sub>OL2</sub>	Output Low Voltage	$V_{CC} > 1.8V$ , $I_{OL} = 150\mu A$		0.2	V
V <sub>OH2</sub>	Output High Voltage	$V_{CC} > 1.8V$ , $I_{OH} = -100\mu A$	V <sub>CC</sub> - 0.2V		V

# PIN CAPACITANCE(2)

 $T_A = 25^{\circ}C$ , f = 1 MHz,  $V_{CC} = 5V$ 

Symbol	Test Conditions	Max	Units	Conditions
C <sub>OUT</sub>	Output Capacitance (SO)	8	pF	V <sub>OUT</sub> = 0 V
C <sub>IN</sub>	Input Capacitance (CS, SCK, SI, WP, HOLD)	6	рF	$V_{IN} = 0 V$

#### Note:

- (1) The DC input voltage on any pin should not be lower than -0.5V or higher than  $V_{CC}$  + 0.5V. During transitions, the voltage on any pin may undershoot to no less than -1.5V or overshoot to no more than  $V_{CC}$  + 1.5V, for periods of less than 20ns.
- (2) These parameters are tested initially and after a design or process change that affects the parameter according to appropriate AEC-Q100 and JEDEC test methods.
- (3)  $V_{IL}$  and  $V_{IH}$  are reference values and are not tested.



# A.C. CHARACTERISTICS

		CAT250XX-1.8		CAT	250XX		
		1.8V-5.5V 2.5V-5.5V		′-5.5V	Test		
SYMBOL	PARAMETER	Min.	Max.	Min.	Max.	Conditions	UNITS
tsu	Data Setup Time	30		20		·	ns
tH	Data Hold Time	30		20			ns
twн	SCK High Time	75		40			ns
tw∟	SCK Low Time	75		40			ns
fsck	Clock Frequency	DC	5	DC	10		MHz
tLZ	HOLD to Output Low Z		50		50		ns
t <sub>RI</sub> <sup>(1)</sup>	Input Rise Time		2		2		μs
t <sub>FI</sub> <sup>(1)</sup>	Input Fall Time		2		2		μs
thD	HOLD Setup Time	0		0			ns
tcD	HOLD Hold Time	10		10			ns
twc <sup>(4)</sup>	Write Cycle Time		5		5	$C_L = 50pf$	ms
t∨	Output Valid from Clock Low		75		40		ns
tHO	Output Hold Time	0		0			ns
tois	Output Disable Time		50		20		ns
tHZ	HOLD to Output High Z		100		25		ns
tcs	CS High Time	50		15			ns
tcss	CS Setup Time	50		15			ns
tсsн	CS Hold Time	50		15			ns
twps	WP Setup Time	10		10			ns
twph	WP Hold Time	10		10			ns

# Power-Up Timing<sup>(1)(3)</sup>

Symbol Parameter		Max.	Units
tpur	Power-up to Read Operation	1	ms
t <sub>PUW</sub>	Power-up to Write Operation	1	ms

#### NOTE:

(1) This parameter is tested initially and after a design or process change that affects the parameter.

(2) AC Test Conditions:

Input Pulse Voltages: 0.3V<sub>CC</sub> to 0.7V<sub>CC</sub>

Input rise and fall times: ≤10ns

Input and output reference voltages: 0.5V<sub>CC</sub>

Output load: current source IOL max/IOH max; C<sub>L</sub>=50pF

- (3) t<sub>PUR</sub> and t<sub>PUW</sub> are the delays required from the time V<sub>CC</sub> is stable until the specified operation can be initiated.
- (4) t<sub>WC</sub> is the time from the rising edge of  $\overline{\text{CS}}$  after a valid write sequence to the end of the internal write cycle.



# **FUNCTIONAL DESCRIPTION**

The CAT25320 supports the SPI bus data transmission protocol. The synchronous Serial Peripheral Interface (SPI) helps the CAT25320 to interface directly with many of today's popular microcontrollers. The CAT25320 contains an 8-bit instruction register. (The instruction set and the operation codes are detailed in the instruction set table)

After the device is selected with  $\overline{CS}$  going low, the first byte will be received. The part is accessed via the SI pin, with data being clocked in on the rising edge of SCK. The first byte contains one of the six op-codes that define the operation to be performed.

# PIN DESCRIPTION

#### SI: Serial Input

SI is the serial data input pin. This pin is used to input all opcodes, byte addresses, and data to be written to the CAT25320. Input data is latched on the rising edge of the serial clock.

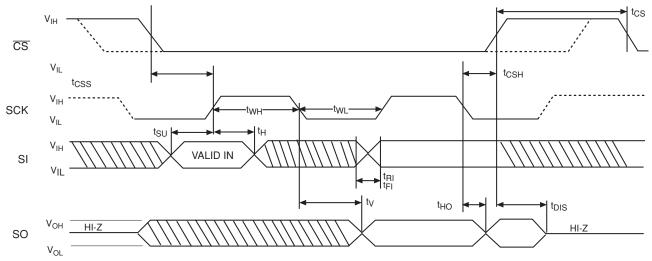
#### **SO: Serial Output**

SO is the serial data output pin. This pin is used to transfer data out of the CAT25320. During a read cycle, data is shifted out on the falling edge of the serial clock.

#### **SCK: Serial Clock**

SCK is the serial clock pin. This pin is used to synchronize

Figure 1. Sychronous Data Timing



Note: Dashed Line= mode (1, 1) — — —

# **INSTRUCTION SET**

Instruction	Opcode	Operation		
WREN	0000 0110	Enable Write Operations		
WRDI	0000 0100	Disable Write Operations		
RDSR	0000 0101	Read Status Register		
WRSR	0000 0001	Write Status Register		
READ	0000 0011	Read Data from Memory		
WRITE	0000 0010	Write Data to Memory		



the communication between the microcontroller and the CAT25320. Opcodes, byte addresses, or data present on the SI pin are latched on the rising edge of the SCK. Data on the SO pin is updated on the falling edge of the SCK.

# **CS**: Chip Select

CS is the Chip select pin. CS low enables the CAT25320 and CS high disables the CAT25320. CS high takes the SO output pin to high impedance and forces the devices into a Standby Mode (unless an internal write operation is underway). A high to low transition on CS is required prior to any sequence being initiated. A low to high transition on CS after a valid write sequence is what initiates an internal write cycle.

#### WP: Write Protect

WP is the Write Protect pin. The Write Protect pin will allow normal read/write operations when held high. When WP is tied low and the WPEN bit in the status register is set to "1", all write operations to the status register are inhibited. WP going low while CS is still low

will interrupt a write to the status register. If the internal write cycle has already been initiated,  $\overline{WP}$  going low will have no effect on any write operation to the status register. The  $\overline{WP}$  pin function is blocked when the WPEN bit is set to 0. Figure 10 illustrates the  $\overline{WP}$  timing sequence during a write operation.

#### **HOLD**: Hold

The  $\overline{HOLD}$  pin is used to pause transmission to the CAT25320 while in the middle of a serial sequence without having to re-transmit entire sequence at a later time. To pause,  $\overline{HOLD}$  must be brought low while SCK is low. The SO pin is in a high impedance state during the time the part is paused, and transitions on the SI pins will be ignored. To resume communication,  $\overline{HOLD}$  is brought high, while SCK is low. ( $\overline{HOLD}$  should be held high any time this function is not being used.)  $\overline{HOLD}$  may be tied high directly to  $V_{CC}$  or tied to  $V_{CC}$  through a resistor. Figure 9 illustrates hold timing sequence.

#### STATUS REGISTER

7	6	5	4	3	2	1	0
WPEN	X	Х	Χ	BP1	BP0	WEL	RDY

#### **BLOCK PROTECTION BITS**

Status R	egister Bits	Array Address	Protection
BP1	BP0	Protected	
0	0	None	No Protection
0	1	0C00-0FFF	Quarter Array Protection
1	0	800-0FFF	Half Array Protection
1	1	0000-0FFF	Full Array Protection

WPEN	WP	WEL	Protected Blocks	Unprotected Blocks	Status Register
0	X	0	Protected	Protected	Protected
0	X	1	Protected	Writable	Writable
1	Low	0	Protected	Protected	Protected
1	Low	1	Protected	Writable	Protected
Х	High	0	Protected	Protected	Protected
Х	High	1	Protected	Writable	Writable



# STATUS REGISTER

The Status Register indicates the status of the device.

The RDY (Ready) bit indicates whether the CAT25320 is busy with a write operation. When set to 1 a write cycle is in progress and when set to 0 the device indicates it is ready. This bit is read only.

The WEL (Write Enable) bit indicates the status of the write enable latch. When set to 1, the device is in a Write Enable state and when set to 0 the device is in a Write Disable state. The WEL bit can only be set by the WREN instruction and can be reset by the WRDI instruction.

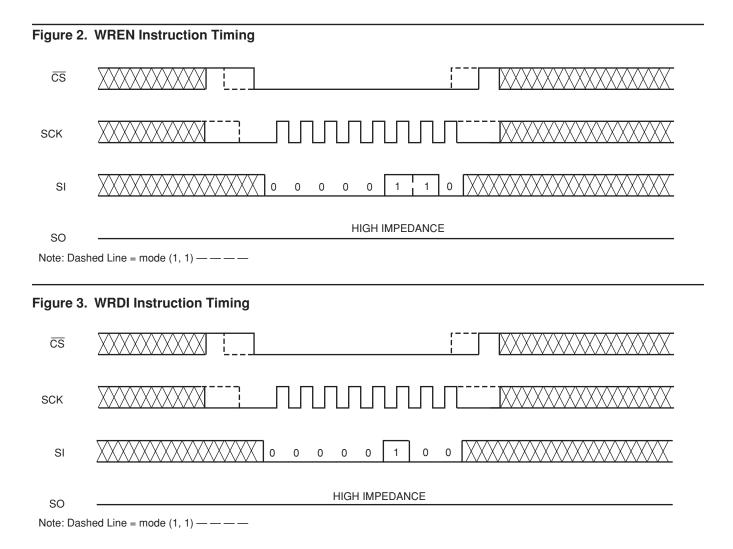
The BP0 and BP1 (Block Protect) bits indicate which blocks are currently protected. These bits are set by the user issuing the WRSR instruction. The user is allowed to protect quarter of the memory, half of the memory or the entire memory by setting these bits. Once protected the user may only read from the protected portion of the array. These bits are non-volatile.

The WPEN (Write Protect Enable) is an enable bit for the  $\overline{WP}$  pin. The  $\overline{WP}$  pin and WPEN bit in the status register control the programmable hardware write protect feature. Hardware write protection is enabled when  $\overline{WP}$  is low and WPEN bit is set to high. The user cannot write to the status register (including the block protect bits and the WPEN bit) and the block protected sections in the memory array when the chip is hardware write protected. Only the sections of the memory array that are not block protected can be written. Hardware write protection is disabled when either WP pin is high or the WPEN bit is zero.

# **DEVICE OPERATION**

#### Write Enable and Disable

The CAT25320 contains a write enable latch. This latch must be set before any write operation. The device powers up in a write disable state when  $V_{\rm cc}$  is applied. WREN instruction will enable writes (set the latch) to the device. WRDI instruction will disable writes (reset the latch) to the device. Disabling writes will protect the device against inadvertent writes.





#### **READ Sequence**

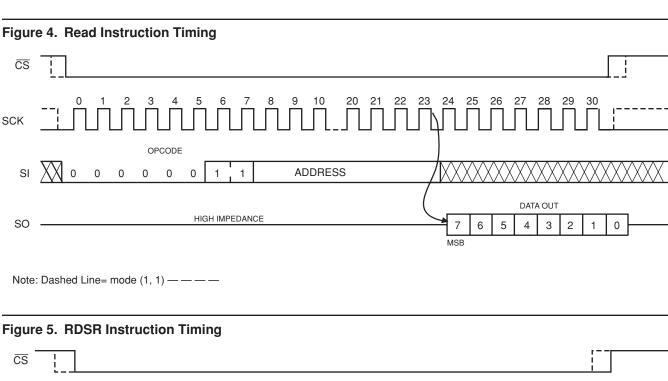
The part is selected by pulling  $\overline{CS}$  low. The 8-bit read instruction is transmitted to the CAT25320, followed by the 16-bit address (the four most significant bits are don't care).

After the correct read instruction and address are sent, the data stored in the memory at the selected address is shifted out on the SO pin. The data stored in the memory at the next address can be read sequentially by continuing to provide clock pulses. The internal address pointer is automatically incremented to the next higher address after each byte of data is shifted out. When the highest address, FFFh is reached, the address counter rolls over to 0000h allowing the read cycle to be continued indefinitely. The read operation is terminated by pulling the  $\overline{\text{CS}}$  high. Read sequece is illustrated in Figure 4.

To read the status register, RDSR instruction should be sent. The contents of the status register are shifted out on the SO line. The status register may be read at any time even during a write cycle. Reading status register is illustrated in Figure 5.

#### **WRITE Sequence**

The CAT25320 powers up in a Write Disable state. Prior to any write instructions, the WREN instruction must be sent to CAT25320. The device goes into Write enable state by pulling the  $\overline{CS}$  low and then clocking the WREN instruction into CAT25320. The  $\overline{CS}$  must be brought high after the WREN instruction to enable writes to the device. If the write operation is initiated immediately after the WREN instruction without  $\overline{CS}$  being brought high, the data will not be written to the array because the write enable latch will not have been properly set. Also, for a successful write operation the address of the memory location(s) to be programmed must be outside the protected address field location selected by the block protection level.



Note: Dashed Line= mode (1, 1) -----



#### **Byte Write**

Once the device is in a Write Enable state, the user may proceed with a write sequence by setting the  $\overline{CS}$  low, issuing a write instruction via the SI line, followed by the 16-bit address (four most significant bits are don't care), and then the data to be written. Programming will start after the  $\overline{CS}$  is brought high. Figure 6 illustrates byte write sequence.

During an internal write cycle, all commands will be ignored except the RDSR (Read Status Register) instruction.

The Status Register can be read to determine if the write cycle is still in progress. If Bit 0 of the Status Register is set at 1, write cycle is in progress. If Bit 0 is set at 0, the device is ready for the next instruction.

#### **Page Write**

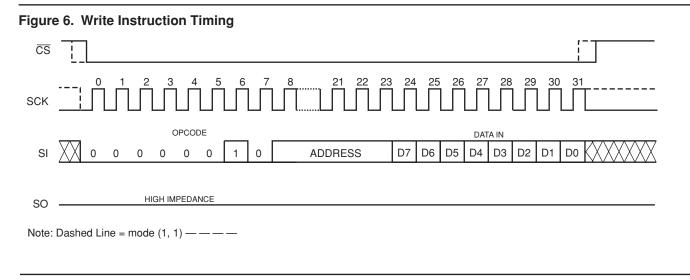
The CAT25320 features page write capability. After the first initial byte the host may continue to write up to 64 bytes of data to the CAT25320. After each byte of data is received, six lower order address bits are internally incremented by one; the high order bits of address will remain constant. The only restriction is that the 64 bytes must reside on the same page. If the address counter reaches the end of the page and clock continues, the counter will "roll over" to the first address of the page and overwrite any data that may have been written. The CAT25320 is automatically returned to the write disable state at the completion of the write cycle. Figure 8 illustrates the page write sequence.

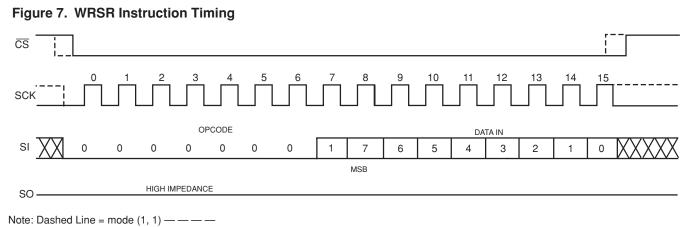
#### **Status Register Write**

To write to the status register, the WRSR instruction should be sent. Only Bit 2, Bit 3 and Bit 7 of the status register can be written using the WRSR instruction. Figure 7 illustrates the sequence of writing to status register.

#### **DESIGN CONSIDERATIONS**

The CAT25320 powers up in a write disable state and in a low power standby mode. A WREN instruction must be issued to perform any writes to the device after power up. After power up  $\overline{CS}$  must be brought low to enter a ready state and receive an instruction. After a successful byte/page write or status register write the CAT25320 goes into







a write disable mode.  $\overline{\text{CS}}$  must be set high after the proper number of clock cycles to start an internal write cycle. Access to the array during an internal write cycle is ignored and programming is continued. On power up, SO is in a high impedance.

If an invalid code is received, no data will be shifted into the CAT25320 and the serial output pin (SO) will remain in a high impedance state until the falling edge of  $\overline{\text{CS}}$  is detected again.

Figure 8. Page Write Instruction Timing

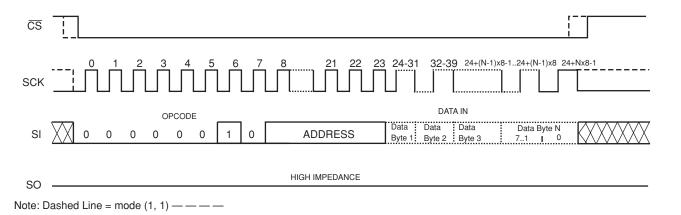


Figure 9. HOLD Timing

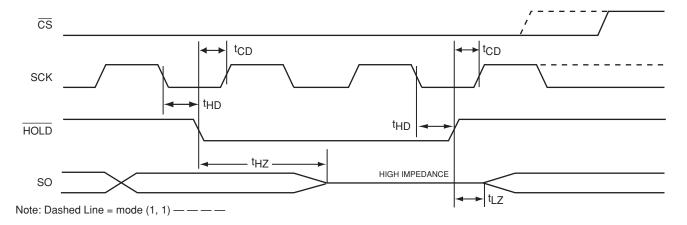
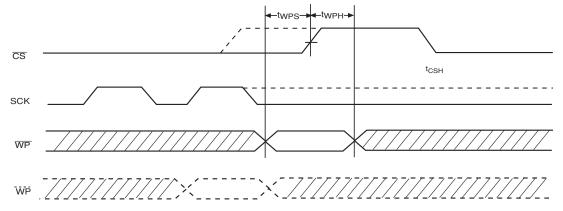
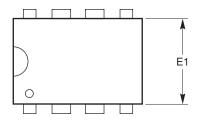


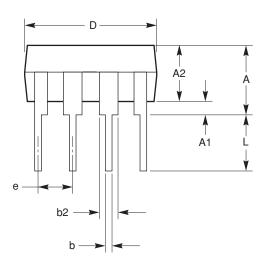
Figure 10. WP Timing

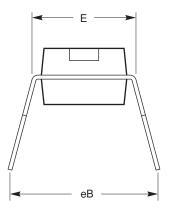




# 8-LEAD 300 MIL WIDE PLASTIC DIP (L)







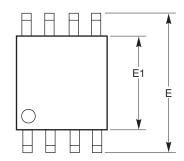
SYMBOL	MIN	NOM	MAX
Α	0.120		0.210
A1	0.015		
A2	0.115	0.130	0.195
b	0.014	0.018	0.022
b2	0.045	0.060	0.070
D	0.355	0.365	0.400
D2	0.300		0.325
E	0.300	0.310	0.325
E1	0.240	0.250	0.280
е		0.100 BSC	
eB			0.430
L	0.115	0.130	0.150

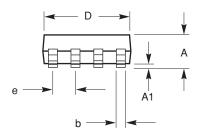
#### Notes:

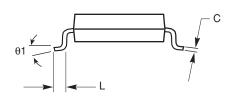
- 1. Complies with JEDEC Standard MS001.
- 2. All dimensions are in inches.
- 3. Dimensioning and tolerancing per ANSI Y14.5M-1982



# 8-LEAD 150 MIL WIDE SOIC (V)







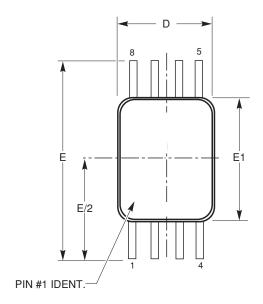
SYMBOL	MIN	NOM	MAX
A1	0.0040		0.0098
A2	0.0532		0.0688
b	0.013		0.020
С	0.0075		0.0098
D	0.1890		0.1968
Е	02284		0.2440
E1	0.149		0.1574
е		0.050 BSC	
f	0.0099		0.0196
θ1	0°		8°

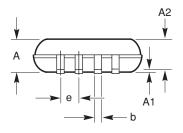
#### Notes:

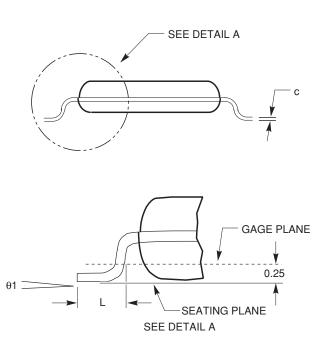
- Complies with JEDEC specification MS-012 dimensions. All linear dimensions in millimeters.



# 8-LEAD TSSOP (Y)







SYMBOL	MIN	NOM	MAX
Α			1.20
A1	0.05		0.15
A2	0.80	0.90	1.05
b	0.19		0.30
С	0.09		0.20
D	2.90	3.00	3.10
E	6.30	6.4	6.50
E1	4.30	4.40	4.50
е		0.65 BSC	
L	0.50	0.60	0.75
θ1	0.00		8.00

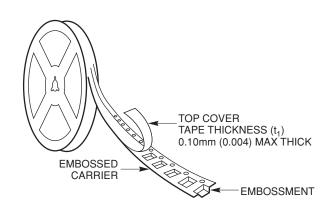
# Notes:

1. All dimensions in millimeters.

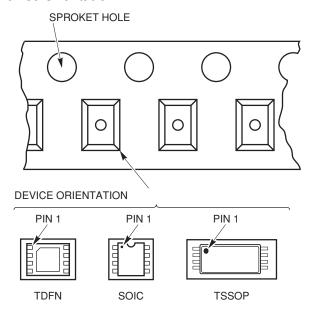


# **TAPE AND REEL**

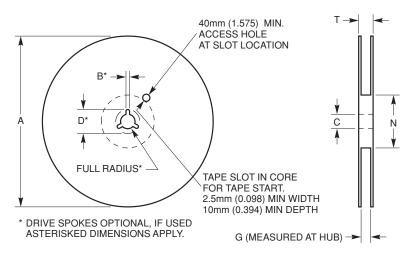
# **Direction of Feed**



# **Device Orientation**



#### Reel Dimensions(1)



#### **Embossed Carrier Dimensions**

TAPE		Α						
SIZE	MAX	QTY/REEL	B MIN	С	D* MIN	N MIN	G	T MAX
12MM	330 (13.00)	3000	1.5 (0.059)	12.80 (0.504) 13.20 (0.5200)	20.2 (0.795)	50 (1.969)	12.4 (0.488) 14.4 (0.558)	<u>18.4</u> (0.724)

# Component/Tape Size Cross-Reference

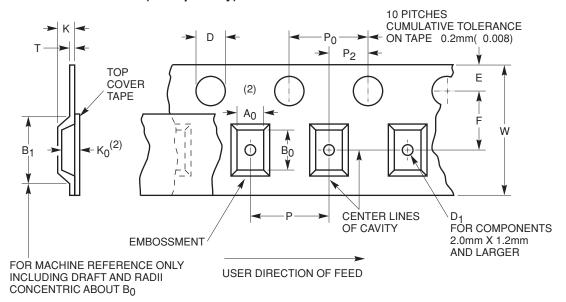
Component	Package Type	Tape Size (W)	Part Pitch (P)	
8L SOIC, TSSOP	V, Y	12mm	8mm	

#### Notes:

(1) Metric dimensions will govern; English measurements rounded, for reference only and in parentheses.



# **Embossed Carrier Dimensions (12 Pape Only)**



# Embossed Tape—Constant Dimensions(1)

Tape Sizes	D	E	$P_{0}$	T Max.	D1 Min.	$A_0 B_0 K_0^{(2)}$
10mm	1.5 (0.059)	1.65 (0.065)	3.9 (0.153)	400	1.5	
12mm	1.6 (0.063)	1.85 (0.073)	4.1 (0.161)	(0.016)	(0.059)	

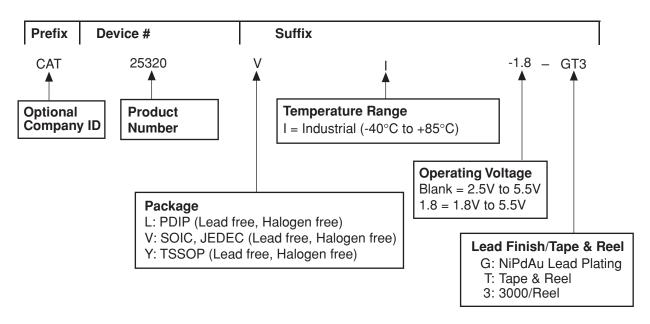
# Embossed Tape—Variable Dimensions(1)

Tape Sizes	B <sub>1</sub> Max.	F	K Max.	P <sub>2</sub>	R Min.	W	Р
12mm	8.2	5.45 (0.0215)	4.5	1.95 (0.077)	30	11.7 (0.460)	<u>7.9 (0.275)</u>
12111111	(0.0323)	5.55 (0.0219)	(0.177)	2.05 (0.081)	(1.181)	12.3 (0.484)	8.1 (0.355)

#### Note

- (1) Metric dimensions will govern; English measurements rounded, for reference only and in parentheses.
- (2) A<sub>0</sub> B<sub>0</sub> K<sub>0</sub> are determined by component size. The clearance between the component and the cavity must be within 0.05 (0.002) min. to 0.65 (0.026) max. for 12mm tape, 0.05 (0.002) min. to 0.90 (0.035) max. for 16mm tape, and 0.05 (0.002) min. to 1.00 (0.039) max. for 24mm tape and larger. The component cannot rotate more than 20° within the determined cavity, see Component Rotation.





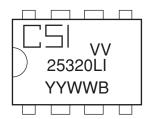
#### Notes:

(1) The device used in the above example is a CAT25320VI-1.8GT3 (SOIC, Industrial Temperature, 1.8 Volt to 5.5 Volt Operating Voltage, Tape & Reel)



# **PACKAGE MARKING**

# 8-Lead PDIP



CSI = Catalyst Semiconductor, Inc.

VV = Voltage Range

1.8V - 5.5V = 182.5V - 5.5V = Blank

25320L = Device Code

I = Temperature Range

YY = Production Year

WW = Production Week

B = Product Revision

# 8-Lead SOIC



CSI = Catalyst Semiconductor, Inc.

VV = Voltage Range

1.8V - 5.5V = 18

2.5V - 5.5V = Blank

25320V = Device Code

I = Temperature Range

YY = Production Year

WW = Production Week

B = Product Revision

# 8-Lead TSSOP



Y = Production Year

M = Production Month

B = Die Revision

25320 = Device Code

I = Industrial Temperature Range

V = Voltage Range

1.8V - 5.5V = 8

2.5V - 5.5V = Blank

# **REVISION HISTORY**

Date	Rev.	Reason		
12/20/05	А	Initial Issue		
03/21/06	В	Update D.C. Operating Characteristics Update A.C. Characteristics Update Pin Description		

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